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April 2013

FQP47P06

P-Channel QFET® MOSFET

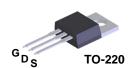
- 60 V, - 47 A, 26 mΩ

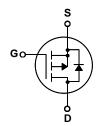
Description

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconducto®'s proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 47 A, 60 V, $R_{DS(on)}$ = 26 m Ω @ V_{GS} = 10 V, I_D = 23.5 A
- Low Gate Charge (Typ. 84 nC)
- Low Crss (yp. 320 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temrature Rating.





Absolute Maximum Ratings $T_C = 25$ °C unless otherwise noted

Symbol	Parameter		FQP47P06	Unit
V _{DSS}	Drain-Source Voltage		-60	V
I _D	Drain Current - Continuous (T _C = 25	°C)	-47	А
	- Continuous (T _C = 10	0°C)	-33.2	А
I _{DM}	Drain Current - Pulsed	(Note 1)	-188	А
V _{GSS}	Gate-Source Voltage		± 25	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	820	mJ
I _{AR}	Avalanche Current	(Note 1)	-47	А
E _{AR}	Repetitive Avalanche Energy	(Note 1)	16	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	-7.0	V/ns
P_D	Power Dissipation (T _C = 25°C) - Derate above 25°C		160	W
			1.06	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FQP47P06	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.94	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

$ \begin{array}{c} BV_{DSS} \\ \Delta T_{J} \\ Coefficient \\ \\ SS \\ \Delta T_{J} \\ Coefficient \\ \\ SS \\ \Delta T_{J} \\ Coefficient \\ \\ SS \\ Zero Gate Voltage Drain Current \\ \hline \\ V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V} \\ \hline \\ V_{DS} = -48 \text{ V}, T_{C} = 150^{\circ}\text{C} \\ \hline \\ V_{DS} = -48 \text{ V}, T_{C} = 150^{\circ}\text{C} \\ \hline \\ V_{DS} = -48 \text{ V}, T_{C} = 150^{\circ}\text{C} \\ \hline \\ V_{DS} = -25 \text{ V}, V_{DS} = 0 \text{ V} \\ \hline \\ V_{DS} = -25 \text{ V}, V_{DS} = 0 \text{ V} \\ \hline \\ V_{DS} = -25 \text{ V}, V_{DS} = 0 \text{ V} \\ \hline \\ V_{DS} = -25 \text{ V}, V_{DS} = 0 \text{ V} \\ \hline \\ V_{DS} = -25 \text{ V}, V_{DS} = 0 \text{ V} \\ \hline \\ V_{DS} = -25 \text{ V}, V_{DS} = 0 \text{ V} \\ \hline \\ V_{DS} = -25 \text{ V}, V_{DS} = 0 \text{ V} \\ \hline \\ V_{DS} = -25 \text{ V}, V_{DS} = 0 \text{ V} \\ \hline \\ V_{DS} = -25 \text{ V}, V_{DS} = 0 \text{ V} \\ \hline \\ V_{DS} = -25 \text{ V}, V_{DS} = 0 \text{ V} \\ \hline \\ V_{DS} = -25 \text{ V}, V_{DS} = 0 \text{ V} \\ \hline \\ V_{DS} = -25 \text{ V}, V_{DS} = 0 \text{ V} \\ \hline \\ V_{DS} = -23.5 \text{ A} \\ \hline \\ V_{DS} = -23.5 \text{ A} \\ \hline \\ V_{DS} = -23.5 \text{ A} \\ \hline \\ V_{DS} = -25 \text{ V}, V_{DS} = 0 \text{ V} \\ \hline \\ V_{DS} = -23.5 \text{ A} \\ \hline \\ V_{DS} = -25 \text{ V}, V_{DS} = 0 \text{ V} \\ \hline \\ V_{DS} = -25 $		Parameter	Test Conditions	Min	Тур	Max	Unit
VDSS Drain-Source Breakdown Voltage $V_{GS} = 0 \text{ V}$, $I_{D} = -250 \mu\text{A}$ -60 $$ V_{C} BVDSS AT User Coefficient Ip = -250 μA, Referenced to 25°C $$ -0.06 $$ V_{C} SSS Zero Gate Voltage Drain Current $V_{DS} = -60 \text{ V}$, $V_{GS} = 0 \text{ V}$ $$	Off Cha	aracteristics					
$ \begin{array}{c} BV_{DSS} \\ \Delta T_{J} \\ Coefficient \\ \\ SS \\ \Delta T_{J} \\ Coefficient \\ \\ SS \\ \Delta T_{J} \\ Coefficient \\ \\ SS \\ Zero Gate Voltage Drain Current \\ \hline \\ V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V} \\ \hline \\ V_{DS} = -48 \text{ V}, T_{C} = 150^{\circ}\text{C} \\ \hline \\ V_{DS} = -48 \text{ V}, T_{C} = 150^{\circ}\text{C} \\ \hline \\ V_{DS} = -48 \text{ V}, T_{C} = 150^{\circ}\text{C} \\ \hline \\ V_{DS} = -25 \text{ V}, V_{DS} = 0 \text{ V} \\ \hline \\ V_{DS} = -25 \text{ V}, V_{DS} = 0 \text{ V} \\ \hline \\ V_{DS} = -25 \text{ V}, V_{DS} = 0 \text{ V} \\ \hline \\ V_{DS} = -25 \text{ V}, V_{DS} = 0 \text{ V} \\ \hline \\ V_{DS} = -25 \text{ V}, V_{DS} = 0 \text{ V} \\ \hline \\ V_{DS} = -25 \text{ V}, V_{DS} = 0 \text{ V} \\ \hline \\ V_{DS} = -25 \text{ V}, V_{DS} = 0 \text{ V} \\ \hline \\ V_{DS} = -25 \text{ V}, V_{DS} = 0 \text{ V} \\ \hline \\ V_{DS} = -25 \text{ V}, V_{DS} = 0 \text{ V} \\ \hline \\ V_{DS} = -25 \text{ V}, V_{DS} = 0 \text{ V} \\ \hline \\ V_{DS} = -25 \text{ V}, V_{DS} = 0 \text{ V} \\ \hline \\ V_{DS} = -25 \text{ V}, V_{DS} = 0 \text{ V} \\ \hline \\ V_{DS} = -23.5 \text{ A} \\ \hline \\ V_{DS} = -23.5 \text{ A} \\ \hline \\ V_{DS} = -23.5 \text{ A} \\ \hline \\ V_{DS} = -25 \text{ V}, V_{DS} = 0 \text{ V} \\ \hline \\ V_{DS} = -23.5 \text{ A} \\ \hline \\ V_{DS} = -25 \text{ V}, V_{DS} = 0 \text{ V} \\ \hline \\ V_{DS} = -25 $	BV _{DSS}		V _{GS} = 0 V, I _D = -250 μA	-60			V
Zero Gate Voltage Drain Current V _{DS} = -48 V, T _C = 150°C -10 μ/V _{DS} = -48 V, T _C = 150°C -10 μ/V _{DS} = -25 V, V _{DS} = 0 V -100 n/V _{DS} = -25 V, V _{DS} = 0 V 100 n/V _{DS} = -25 V, V _{DS} = 0 V 100 n/V _{DS} = -25 V, V _{DS} = 0 V 100 n/V _{DS} = -25 V, V _{DS} = 0 V 100 n/V _{DS} = -25 V, V _{DS} = 0 V 100 n/V _{DS} = -25 V, V _{DS} = 0 V 100 n/V _{DS} = -25 V, V _{DS} = 0 V 100 n/V _{DS} = -20 V, V _{DS} = -25 V, V _{DS} = 0 V, V _{DS} = 0 V, V _{DS} = -25 V, V _{DS} = 0 V, V _{DS} = 0 V, V _{DS} = 0 V, V _{DS} = -25 V, V _{DS} = 0 V	ΔBV _{DSS}	Breakdown Voltage Temperature			-0.06		V/°C
V _{DS} = -48 V, I _C = 150°C -10 μ/sss Gate-Body Leakage Current, Forward V _{GS} = -25 V, V _{DS} = 0 V -100 n/sss Gate-Body Leakage Current, Reverse V _{GS} = 25 V, V _{DS} = 0 V 100 n/s	I _{DSS}	Zero Onto Valta va Basis Oceana	V _{DS} = -60 V, V _{GS} = 0 V			-1	μΑ
Sess Gate-Body Leakage Current, Reverse V _{GS} = 25 V, V _{DS} = 0 V 100 n/s		Zero Gate Voltage Drain Current	V _{DS} = -48 V, T _C = 150°C			-10	μΑ
On Characteristics GS(th) Gate Threshold Voltage $V_{DS} = V_{GS}$, $I_{D} = -250 \mu\text{A}$ -2.0 -4.0 V DS(on) Static Drain-Source On-Resistance $V_{GS} = -10 \text{V}$, $I_{D} = -23.5 \text{A}$ 0.021 0.026 Ω Con-Resistance $V_{DS} = -30 \text{V}$, $I_{D} = -23.5 \text{A}$ 21 S Dynamic Characteristics Input Capacitance $V_{DS} = -25 \text{V}$, $V_{GS} = 0 $	I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = -25 V, V _{DS} = 0 V			-100	nA
GS(th) Gate Threshold Voltage $V_{DS} = V_{GS}$, $I_D = -250 \mu A$ -2.0 -4.0 V DS(on) Static Drain-Source On-Resistance $V_{GS} = -10 \text{V}$, $I_D = -23.5 \text{A}$ 0.021 0.026 Ω PS Forward Transconductance $V_{DS} = -30 \text{V}$, $I_D = -23.5 \text{A}$ (Note 4) 21 S PS Input Capacitance $V_{DS} = -25 \text{V}$, $V_{GS} = 0 \text{V}$, $V_{GS} = 0 $	I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = 25 V, V _{DS} = 0 V			100	nA
GS(th) Gate Threshold Voltage $V_{DS} = V_{GS}$, $I_D = -250 \mu A$ -2.0 -4.0 V DS(on) Static Drain-Source On-Resistance $V_{GS} = -10 \text{V}$, $I_D = -23.5 \text{A}$ 0.021 0.026 Ω PS Forward Transconductance $V_{DS} = -30 \text{V}$, $I_D = -23.5 \text{A}$ (Note 4) 21 S PS Input Capacitance $V_{DS} = -25 \text{V}$, $V_{GS} = 0 \text{V}$, $V_{GS} = 0 $	On Cha	aracteristics					
DS(on) Static Drain-Source On-Resistance $V_{GS} = -10 \text{ V}$, $I_D = -23.5 \text{ A}$ 0.021 0.026 Ω PS Forward Transconductance $V_{DS} = -30 \text{ V}$, $I_D = -23.5 \text{ A}$ (Note 4) 21 S Pynamic Characteristics Input Capacitance $V_{DS} = -25 \text{ V}$, $V_{GS} = 0 \text{ V}$, $I_D = -23.5 \text{ A}$, $I_D =$	V _{GS(th)}	+	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-2.0		-4.0	V
tynamic Characteristics siss Input Capacitance $V_{DS} = -25 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1.0 \text{ MHz}$	R _{DS(on)}		V _{GS} = -10 V, I _D = -23.5 A		0.021	0.026	Ω
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	9 _{FS}	Forward Transconductance	$V_{DS} = -30 \text{ V}, I_D = -23.5 \text{ A}$ (Note 4)		21		S
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Coss	' '	f = 1.0 MHz				pF
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		' '	f = 1.0 MHz				
Turn-On Rise Time $V_{DD} = -30 \text{ V, } I_{D} = -23.5 \text{ A,}$ $C_{DD} = -30 \text{ V, } I_{D} = $	C _{rss}	<u>'</u>			0_0	420	рі
Turn-On Rise Time $R_{G} = 25 \ \Omega$ 450 910 ns		ing Characteristics			020	420	рі
(off) Turn-Off Delay Time 100 210 ns Turn-Off Fall Time (Note 4, 5) 195 400 ns	Switchi	1	V-n = -30 V In = -23 5 A			1	ns
		Turn-On Delay Time			50	110	•
g Total Gate Charge V _{DS} = -48 V, I _D = -47 A, 84 110 nC	Switchi	Turn-On Delay Time Turn-On Rise Time			50 450	110 910	ns
	Switchi $t_{d(on)}$ t_r $t_{d(off)}$	Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time	$R_G = 25 \Omega$		50 450 100	110 910 210	ns
Gate-Source Charge $V_{GS} = -10 \text{ V}$ 18 nC	Switchi $t_{d(on)}$ t_r $t_{d(off)}$	Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time	$R_G = 25 \Omega$		50 450 100 195	110 910 210 400	ns ns
	Switchi td(on) tr tf td(off) tg Qg	Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge	$R_G = 25 \ \Omega$ (Note 4, 5) $V_{DS} = -48 \ V$, $I_D = -47 \ A$,	 	50 450 100 195 84	110 910 210 400 110	ns ns ns
					323	420	
	Switchi td(on) tr td(off) tf Qg Qgs	Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge Gate-Source Charge	$R_G = 25 \Omega$ (Note 4, 5) $V_{DS} = -48 \text{ V}, I_D = -47 \text{ A}, V_{GS} = -10 \text{ V}$	 	50 450 100 195 84 18	110 910 210 400 110	ns ns ns ns
	Switchi td(on) tr td(off) tf Qg Qgs	Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge Gate-Source Charge	$R_G = 25 \Omega$ (Note 4, 5) $V_{DS} = -48 \text{ V}, I_D = -47 \text{ A}, V_{GS} = -10 \text{ V}$	 	50 450 100 195 84 18	110 910 210 400 110	ns ns ns ns
gd Gate-Drain Charge (Note 4, 5) 44 nC	Switchi t _{d(on)} t _r t _{d(off)} t _f Q _g Q _{gs} Q _{gd}	Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge Gate-Source Charge Gate-Drain Charge	$R_G = 25~\Omega \label{eq:reconstruction}$ (Note 4, 5) $V_{DS} = -48~V, I_D = -47~A, \label{eq:vgs}$ $V_{GS} = -10~V \label{eq:vgs}$ (Note 4, 5)	 	50 450 100 195 84 18	110 910 210 400 110	ns ns ns ns
gd Gate-Drain Charge (Note 4, 5) 44 nC Prain-Source Diode Characteristics and Maximum Ratings	Switchi t _{d(on)} t _r t _{d(off)} t _f Q _g Q _{gs} Q _{gd} Drain-S	Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge Gate-Source Charge Gate-Drain Charge	$R_G = 25~\Omega \label{eq:RG}$ (Note 4, 5) $V_{DS} = -48~V,~I_D = -47~A,~V_{GS} = -10~V \label{eq:VDS}$ (Note 4, 5)	 	50 450 100 195 84 18 44	110 910 210 400 110 	ns ns ns ns
Gate-Drain Charge (Note 4, 5) 44 nCertain-Source Diode Characteristics and Maximum Ratings Maximum Continuous Drain-Source Diode Forward Current47 A	$\begin{array}{c} \textbf{Switchi} \\ \textbf{t}_{d(on)} \\ \textbf{t}_{r} \\ \textbf{t}_{d(off)} \\ \textbf{t}_{f} \\ \textbf{Q}_{g} \\ \textbf{Q}_{gs} \\ \textbf{Q}_{gd} \\ \end{array}$	Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge Gate-Source Charge Gate-Drain Charge Source Diode Characteristics ar Maximum Continuous Drain-Source Dio	$R_G = 25 \ \Omega$ $V_{DS} = -48 \ V, \ I_D = -47 \ A,$ $V_{GS} = -10 \ V$ (Note 4, 5) and Maximum Ratings and Forward Current	 	50 450 100 195 84 18 44	110 910 210 400 110 	ns ns ns nc nC
Grain-Source Diode Characteristics and Maximum Ratings Maximum Continuous Drain-Source Diode Forward Current Maximum Pulsed Drain-Source Diode Forward Current	Switchi t _{d(on)} t _r t _{d(off)} t _f Q _g Q _{gs} Q _{gd} Drain-S I _S	Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge Gate-Source Charge Gate-Drain Charge Source Diode Characteristics ar Maximum Continuous Drain-Source Diode Fall Time	$R_G = 25 \Omega$ (Note 4, 5) $V_{DS} = -48 \text{ V}, I_D = -47 \text{ A},$ $V_{GS} = -10 \text{ V}$ (Note 4, 5) and Maximum Ratings ode Forward Current Forward Current	 	50 450 100 195 84 18 44	110 910 210 400 110 	ns ns ns nc nC
Gate-Drain Charge (Note 4, 5) 44 note (Prain-Source Diode Characteristics and Maximum Ratings Maximum Continuous Drain-Source Diode Forward Current Maximum Pulsed Drain-Source Diode Forward Current 47 A Maximum Pulsed Drain-Source Diode Forward Current 48 A Drain-Source Diode Forward Voltage V _{GS} = 0 V, I _S = -47 A 4.0 V	Switchi t _{d(on)} t _r t _{d(off)} t _f Q _g Q _{gs} Q _{gd} Drain-S	Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge Gate-Source Charge Gate-Drain Charge Source Diode Characteristics ar Maximum Continuous Drain-Source Diode F Drain-Source Diode Forward Voltage	$R_{G} = 25 \ \Omega$ $V_{DS} = -48 \ V, I_{D} = -47 \ A,$ $V_{GS} = -10 \ V$ $(Note 4, 5)$ $Note 4, 5$ $Note 5, 5$ $Note 6, 7$ $Note 6, 7$ $Note 6, 7$ $Note 6, 7$ $Note 7, 7$ N	 	50 450 100 195 84 18 44	110 910 210 400 110 -47 -188 -4.0	ns ns ns nC nC

- **Notes:**1. Repetitive Rating : Pulse width limited by maximum junction temperature 2. L = 0.43mH, I_{AS} = -47A, V_{DD} = -25V, R_G = 25 Ω, Starting T_J = 25°C 3. I_{SD} ≤ -47A, di/dt ≤ 300A/µs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C 4. Pulse Test : Pulse width ≤ 300µs, Duty cycle ≤ 2% 5. Essentially independent of operating temperature

Typical Characteristics

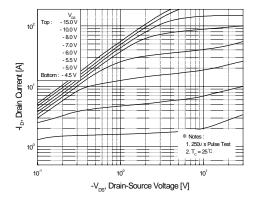


Figure 1. On-Region Characteristics

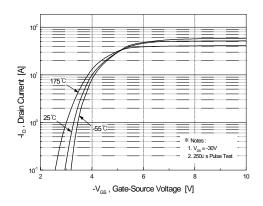


Figure 2. Transfer Characteristics

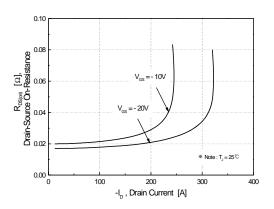


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

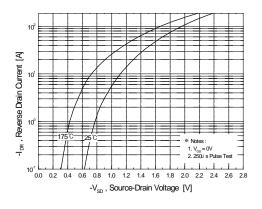


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

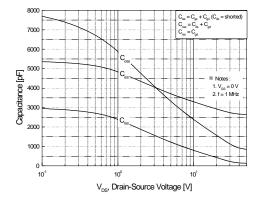


Figure 5. Capacitance Characteristics

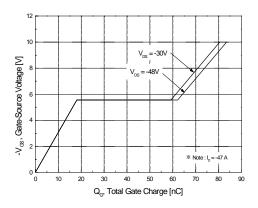


Figure 6. Gate Charge Characteristics

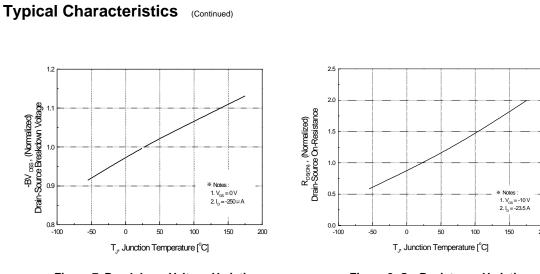


Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature

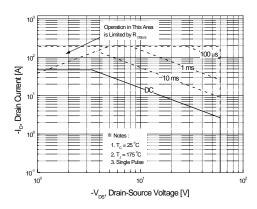


Figure 9. Maximum Safe Operating Area

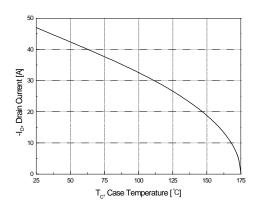


Figure 10. Maximum Drain Current vs. Case Temperature

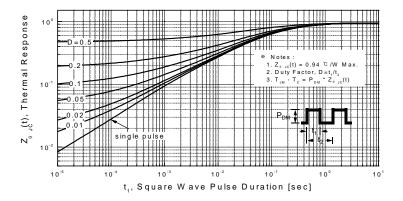
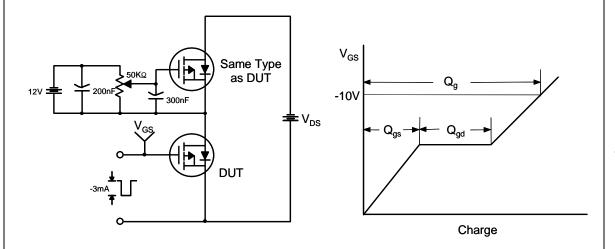
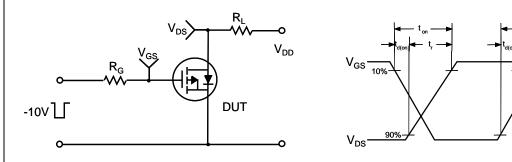


Figure 11. Transient Thermal Response Curve

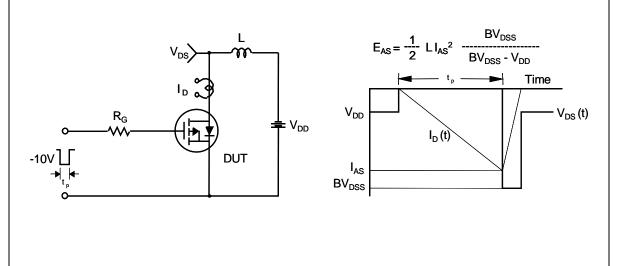
Gate Charge Test Circuit & Waveform



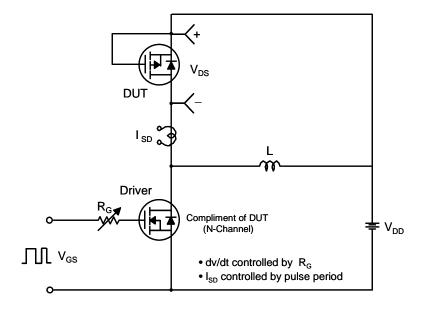
Resistive Switching Test Circuit & Waveforms

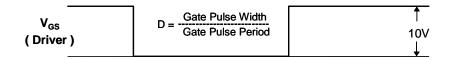


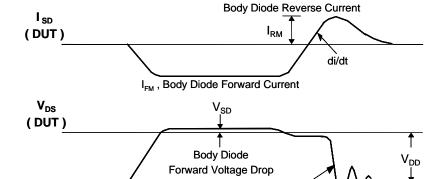
Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveforms



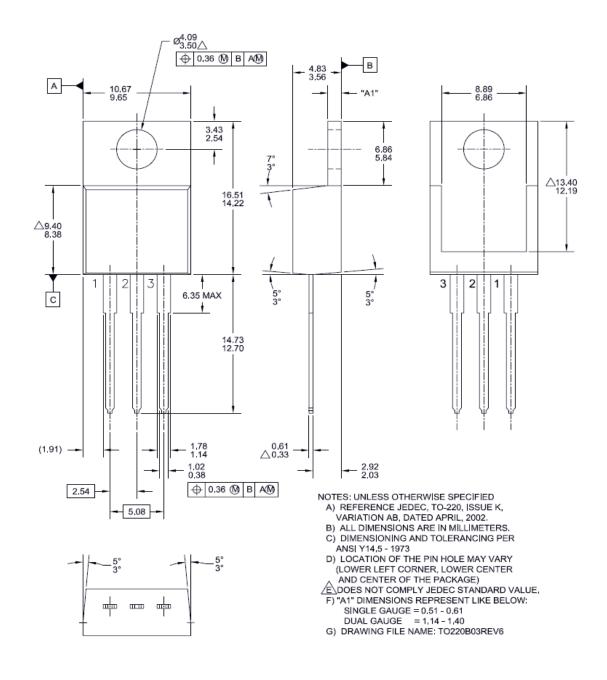




Body Diode Recovery dv/dt

Mechanical Dimensions

TO-220B03



Dimensions in Millimeters





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CorePOWER™ Green FPS™ e-Series™ CROSSVOLT™ Gmax™

CTL™ GTO™ Current Transfer Logic™ IntelliMAX™ DEUXPEED® ISOPLANAR™

Dual Cool™ Marking Small Speakers Sound Louder EcoSPARK® and Better™

MegaBuck™ EfficentMax™ MICROCOUPLER™ ESBC™ MicroFET™

MicroPak™ MicroPak2™ Fairchild[®] MillerDrive™ Fairchild Semiconductor® MotionMax™ FACT Quiet Series™ mWSaver™ OptoHiT™

FACT[®] FAST® OPTOLOGIC® FastvCore™ OPTOPLANAR® FETBench™

(1)_® PowerTrench® PowerXS™

Programmable Active Droop™

 QS^{TM} Quiet Series™ RapidConfigure™

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SignalWise™ SmartMax™ SMART START™

Solutions for Your Success™

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